

AMENDMENTS TO THE CLAIMS:

If entered, this listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1-21 canceled

22. (currently amended) A method to fabricate a two-level DRAM cell requiring a reduced output current, comprising:

providing a capacitor, a natural transistor as pass transistor, and peripheral circuitry to activate and to drive said DRAM cell comprising standard transistors, a current source and an amplifier;

mask the channel of the natural transistor to avoid any impurities caused by ~~at~~ the following ion implant step;

perform ion implant to define threshold voltage of the standard transistors as part of the DRAM cell; and

remove mask from natural transistor and continue standard processes.

23. (original) The method of claim **22** wherein said natural transistor is a PMOS transistor.

24. (original) The method of claim **22** wherein said natural transistor is a CMOS transistor.

25. (original) The method of claim **22** wherein said natural transistor is a NMOS transistor.

26. (currently amended) A method to fabricate a multi-level DRAM cell requiring a reduced output current, comprising:

providing a capacitor, a natural transistor as pass transistor, and peripheral circuitry to activate and to drive said DRAM cell comprising a multiplexer

5 containing transistors to activate a desired voltage level, a transistor to activate a read-out of said DRAM cell, an analog-to digital converter, a current source and an amplifier;

mask the channel of the natural transistor to avoid any impurities caused by ~~the~~ the following ion implant step;

10 perform ion implant to define threshold voltage of the standard transistors as part of the DRAM cell; and

remove mask from natural transistor and continue standard processes.

27. (original) The method of claim **26** wherein said natural transistor is a PMOS transistor.

28. (original) The method of claim **26** wherein said natural transistor is a CMOS transistor.

29. The method of claim **26** wherein said natural transistor is a NMOS transistor.